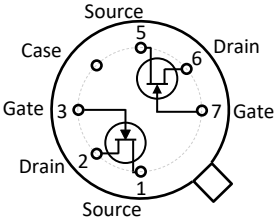
IFNU257 Dual Matched N-Channel JFET

Features

- InterFET N0030L Geometry
- Low Leakage: 4.0pA Typical
- Low Input Capacitance: 5.0pF Typical
- Replacement for U257
- RoHS Compliant
- SMT, TH, and Bare Die Package options.

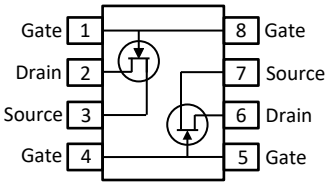
TO-78 Bottom View



Applications

- Wideband Differential Amplifiers
- Audio Amplifiers

SOIC8 Top View



Description

The -25V InterFET IFN257 JFET is targeted for wideband differential amplifier applications. Gate leakages are typically less than 4pA at room temperatures. The TO-78 package is hermetically sealed and suitable for military applications. Custom specifications, matching, and packaging options are available.

Product Summary

Parameters		IFNU235 Min	Unit
BV_{GSS}	Gate to Source Breakdown Voltage	-25	V
I_{DSS}	Drain to Source Saturation Current	5	mA
$V_{GS(off)}$	Gate to Source Cutoff Voltage	-1	V
G_{FS}	Forward Transconductance	4.5	mS

Ordering Information Custom Part and Binning Options Available

Part Number	Description	Case	Packaging
IFNU257	Through-Hole	TO-78	Bulk
SMPU257	Surface Mount	SOIC8	Bulk
SMPU257TR	7" Tape and Reel: Max 500 Pieces 13" Tape and Reel: Max 2,500 Pieces	SOIC8	Minimum 500 Pieces Tape and Reel
IFNU257COT *	Chip Orientated Tray (COT Waffle Pack)	COT	70/Waffle Pack
IFNU257CFT *	Chip Face-up Tray (CFT Waffle Pack)	CFT	70/Waffle Pack

* Bare die packaged options are designed for matched specifications but not 100% tested

Electrical Characteristics

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

Parameters		Value	Unit
V_{RGS}	Reverse Gate Source and Gate Drain Voltage	-25	V
I_{FG}	Continuous Forward Gate Current	50	mA
P_D	Continuous Device Power Dissipation	300	mW
P	Power Derating	4	mW/°C
T_J	Operating Junction Temperature	-55 to 125	°C
T_{STG}	Storage Temperature	-65 to 150	°C

Static Characteristics (@ TA = 25°C, Unless otherwise specified)

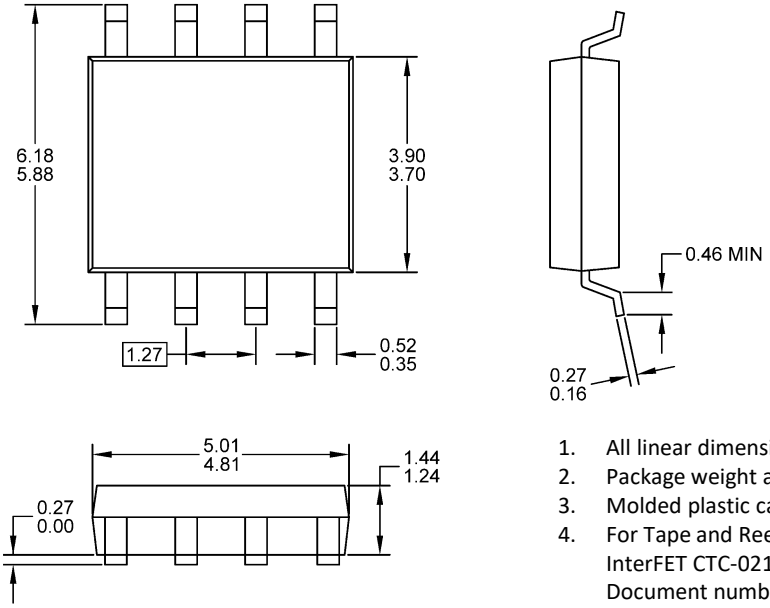
Parameters		Conditions	IFNU257		Unit
			Min	Max	
$V_{(BR)GSS}$	Gate to Source Breakdown Voltage	V_{DS} = 0V, I_G = -1µA	-25		V
I_{GSS}	Gate to Source Reverse Current	V_{GS} = -15V, V_{DS} = 0V, T_A = 25°C V_{GS} = -15V, V_{DS} = 0V, T_A = 150°C		-100 -250	pA nA
$V_{GS(OFF)}$	Gate to Source Cutoff Voltage	V_{DS} = 10V, I_D = 1nA	-1	-5	V
I_{DSS}	Drain to Source Saturation Current	V_{DS} = 10V, V_{GS} = 0V (Pulsed)	5	40	mA

Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified)

Parameters		Conditions	IFNU257		Unit
			Min	Max	
G_{FS}	Forward Transconductance	V_{DS} = 10V, I_D = 5mA, f = 1kHz V_{DS} = 10V, I_D = 5mA, f = 100MHz	4.5 4.5	10 10	mS
G_{OS}	Output Conductance	V_{DS} = 10V, I_D = 5mA, f = 1kHz V_{DS} = 10V, I_D = 5mA, f = 100MHz		200 200	µS
C_{iss}	Input Capacitance	V_{DS} = 10V, I_D = 5mA, f = 1MHz		5	pF
C_{rss}	Reverse Transfer Capacitance	V_{DS} = 10V, I_D = 5mA, f = 1MHz		1.2	pF
e_n	Equivalent Circuit Input Noise Voltage	V_{DS} = 10V, I_D = 5mA, f = 10kHz		30	nV/√Hz
$\lvert V_{GS1} - V_{GS2} \rvert$	Differential Gate Source Voltage	V_{DS} = 10V, I_D = 5mA		100	mV
$\lvert G_{OS1} - G_{OS2} \rvert$	Differential Output Conductance	V_{DS} = 10V, I_D = 5mA		20	µS
$\frac{I_{DSS1}}{I_{DSS2}}$	Co-saturation Drain Current Ratio	V_{DS} = 10V, V_{GS} = 0V	0.85	1	-

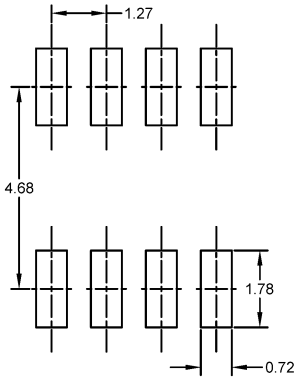
SOIC8 Mechanical and Layout Data

Package Outline Data



1. All linear dimensions are in millimeters.
2. Package weight approximately 0.21 grams
3. Molded plastic case UL 94V-0 rated
4. For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
5. Bulk product is shipped in standard ESD shipping material
6. Refer to JEDEC standards for additional information.

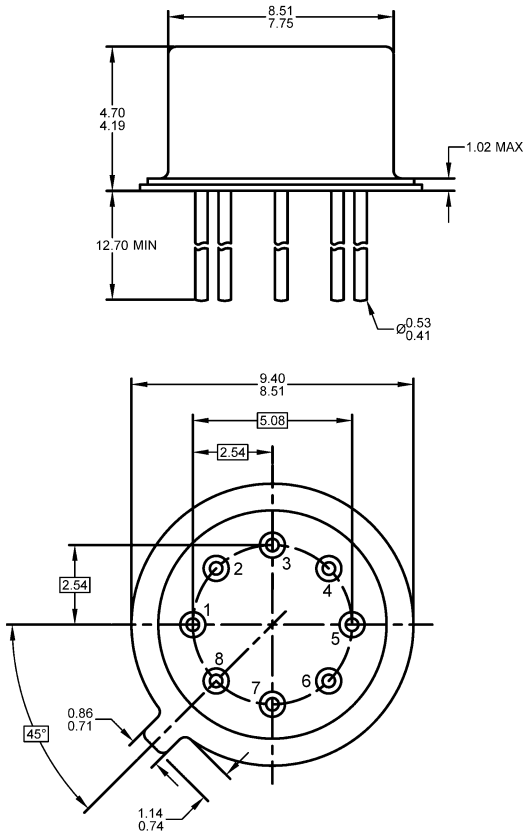
Suggested Pad Layout



1. All linear dimensions are in millimeters.
2. The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.

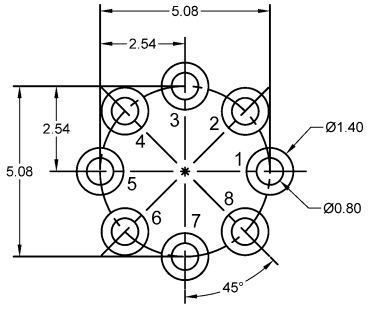
TO-78 Mechanical and Layout Data

Package Outline Data



1. All linear dimensions are in millimeters.
2. Eight leaded device. Not all leads are shown in drawing views.
3. Some package configurations will not populate pin 8 and/or pin 7.
4. Package weight approximately 0.44 grams
5. Bulk product is shipped in standard ESD shipping material
6. Refer to JEDEC standards for additional information.

Suggested Through-Hole Layout



1. All linear dimensions are in millimeters.
2. The suggested land pattern dimensions have been provided as a straight lead reference only. A more robust pattern may be desired for wave soldering and/or bent lead configurations.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

InterFET:
U257